

Octal Bus Buffer MC74LVX541

The MC74LVX541 is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74LVX541 is a noninverting type. When either $\overline{OE1}$ or $\overline{OE2}$ are high, the terminal outputs are in the high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 6.5 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 5.0 \text{ ns}$ (Typ) at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 3.6 V Operating Range
- Low Noise: V_{OLP} = 1.2 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- Chip Complexity: 134 FETs or 33.5 Equivalent Gates
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

• These Devices are Pb-Free and are RoHS Compliant

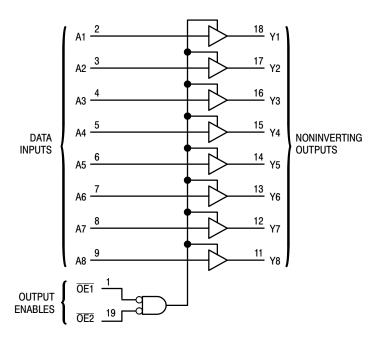


Figure 1. Logic Diagram

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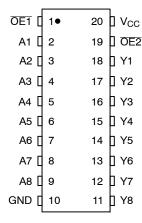




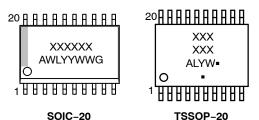


TSSOP-20 DT SUFFIX CASE 948E

PIN ASSIGNMENT



MARKING DIAGRAMS



XXXXXX = Specific Device Code A = Assembly Location

WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

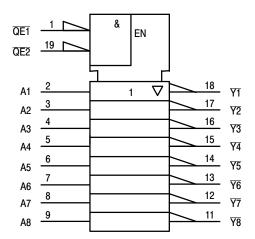


Figure 2. IEC Logic Diagram

FUNCTION TABLE

	Inputs	Output V	
OE1	OE2	A	Output Y
L	L	L	L
L	L	Н	Н
Н	Х	Х	Z
Х	Н	Х	Z

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		- 0.5 to + 6.5	V
V _{in}	DC Input Voltage		- 0.5 to + 6.5	V
V _{out}	DC Output Voltage		-0.5 to V_{CC} + 0.5	V
I _{IK}	Input Diode Current		- 20	mA
I _{OK}	Output Diode Current		± 20	mA
I _{out}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins		± 50	mA
P _D	Power Dissipation in Still Air,	SOIC TSSOP	1302 833	mW
T _{stg}	Storage Temperature		- 65 to + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V _{CC}	DC Supply Voltage		2.0	3.6	V
V _{in}	DC Input Voltage		0	5.5	V
V _{out}	DC Output Voltage		0	V _{CC}	V
T _A	Operating Temperature, All Package Types		-40	+85	°C
t _r , t _f	Input Rise and Fall Time V _{CC} = 3	.3 V ± 0.3 V	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}		A = 25°	С	$T_A = -40$) to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 3.6	1.50 2.0 2.4			1.50 2.0 2.4		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 3.6			0.50 0.80 0.80		0.50 0.80 0.80	V
V _{OH}		$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 \text{ mA}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}		$I_{OL} = 50 \mu A$ $I_{OL} = 50 \mu A$ $I_{OL} = 4 \text{ mA}$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	٧
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 3.6			±0.1		±1.0	μΑ
I _{OZ}	Maximum Three–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	3.6			±0.2 5		±2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	3.6			4.0		40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

				Т	T _A = 25°C			T _A = -40 to 85°C	
Symbol	Parameter	Test Cond	ditions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to Y	V _{CC} = 2.7 V	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.0 7.5	7.0 10.5	1.0 1.0	8.5 12.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		3.5 5.0	5.0 7.0	1.0 1.0	6.0 8.0	
t _{PZL} , t _{PZH}	Output Enable Time, OE to Y	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		6.8 9.3	10.5 14.0	1.0 1.0	12.5 16.0	ns
		V_{CC} = 3.3 \pm 0.3 V R_L = 1 $k\Omega$	$C_L = 15 pF$ $C_L = 50 pF$		4.7 6.2	7.2 9.2	1.0 1.0	8.5 10.5	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Y	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C _L = 50 pF		11.2	15.4	1.0	17.5	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C _L = 50 pF		6.0	8.8	1.0	10.0	
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 2.7 V (Note 1)	C _L = 50 pF			1.5		1.5	ns
		V _{CC} = 3.3 ± 0.3 V (Note 1)	C _L = 50 pF			1.0		1.0	ns
C _{in}	Maximum Input Capacitance				4.0	10		10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High Impedance State)				6.0				pF
		·		Typical @ 25°C, V _{CC} = 5.0 V			0 V	·	
C _{PD}	Power Dissipation Capacitance (Note 2)					18	3		pF

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PLHn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$, $C_L = 50 \text{ pF}$, $V_{CC} = 3.3 \text{ V}$)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.5	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.5	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

SWITCHING WAVEFORMS

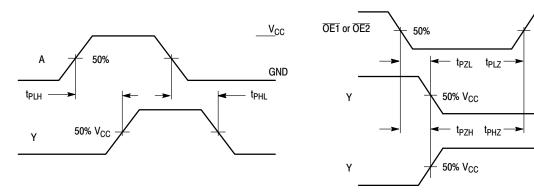
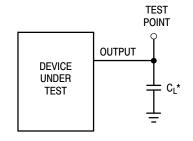


Figure 3.

TEST CIRCUITS



*Includes all probe and jig capacitance

Figure 5.

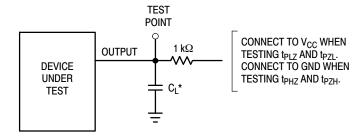


Figure 4.

 V_{CC}

GND

HIGH IMPEDANCE

V_{OL} +0.3 V

V_{OH} -0.3 V

HIGH IMPEDANCE

50%

*Includes all probe and jig capacitance

Figure 6.

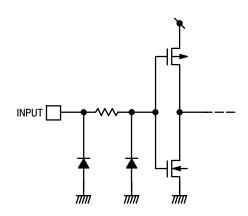


Figure 7. Input Equivalent Circuit

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74LVX541DWG	LVX541	SOIC-20 (Pb-Free)	38 Units / Rail
MC74LVX541DTR2G	LVX 541	TSSOP-20 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

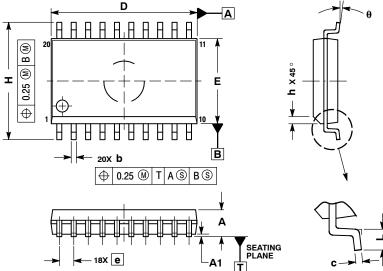




SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015

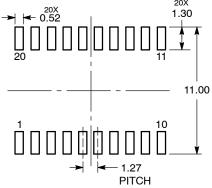
SCALE 1:1



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

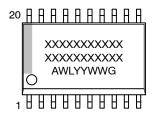
	MILLIMETERS					
DIM	MIN	MAX				
Α	2.35	2.65				
A1	0.10	0.25				
b	0.35	0.49				
С	0.23	0.32				
D	12.65	12.95				
E	7.40	7.60				
е	1.27	BSC				
Н	10.05	10.55				
h	0.25	0.75				
L	0.50	0.90				
A	0 °	7 °				

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOIC-20 WB		PAGE 1 OF 1			

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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